IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

12/C Arndt 8/14/01 A. Dodd

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| Applicant: | Hutter et al. | Art Unit: | 2825 |
| Serial No.: | 09/276,780 | Examiner: | Luu, C. |
| Filing Date: | 03/25/99 | Docket No.: | TI-27203 |
| Title: | MERGED BIPOLAR AND CMOS CIRCUIT AND METHOD | | |

**Amendment under 37 CFR 1.115**

Assistant Commissioner of Patents
Washington, DC 20231

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(A)
I hereby certify that this correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on
8-2-01
Marianna Smith
Marianna Smith

Dear Sir:

The following amendment and remarks are offered in response to the Examiner's Office Action dated 04/11/01. They are respectfully submitted as a full and complete response to that Action.



Please amend the application as follows:

In the claims:

Amend claim 1 to read as follows:

1. (amended) A method for fabricating a BiCMOS integrated circuit, comprising the steps of:

forming in a single implantation step a base region of a bipolar transistor and a p-well of an n-channel MOS transistor; and

forming in a single implantation step a collector contact well of a bipolar transistor and an n-well of a p-channel MOS transistor, said collector contact well



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